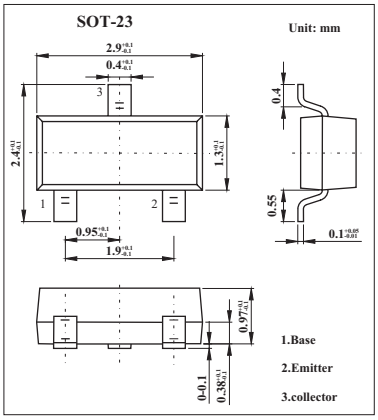
NPN General Purpose Transistor

2SC4617



■ Features

- High h_{FE} : 210 ～ 460 (typ.)
- Low $V_{CE(sat)}$ < 0.5V

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-Emitter Voltage	V_{CEO}	50	V
Collector-Base Voltage	V_{CBO}	50	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Collector Current- Continuous	I_C	100	mA
Power Dissipation *	P_D	125	mW
Jumction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

* Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint.

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector Base Breakdown Voltage	V_{CBO}	I_C = 50uA, I_E = 0	50			V
Collector Emitter Breakdown Voltage	V_{CEO}	I_C = 1.0mA, I_B = 0	50			V
Emitter Base Breakdown Voltage	V_{EBO}	I_E = 50uA, I_C = 0	5.0			V
Collector Cut-off Current	I_{CBO}	I_E = 0 , V_{CB} = 30V			0.5	uA
Emitter Cut-off Current	I_{EBO}	I_B = 0 , V_{EB} = 4.0V			0.5	uA
DC Current Gain *	h_{FE}	I_C = 1.0mA , V_{CE} = 6.0V	120		560	
Collector-Emitter Saturation Voltage *	$V_{CE(sat)}$	I_C = 60mA , I_B = 5.0mA			0.4	V
Transition Frequency	f_T	V_{CE} = 12V , I_C = 2.0mA , f = 30MHz		180		MHz
Output Capacitance	C_{OB}	V_{CB} = 12V , I_C = 0, f = 1MHz		2		pF

* Pulse Test: Pulse With ≤300us, D.C. ≤2%.